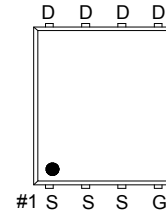
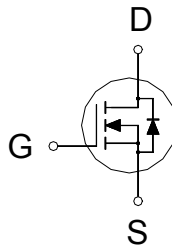




PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	7.2mΩ	30A



G. GATE
D. DRAIN
S. SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ °C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C = 25\text{ °C}$ (Package Limited)	I_D	30	A
	$T_C = 25\text{ °C}$ (Silicon Limited)		71	
	$T_C = 100\text{ °C}$		45	
Pulsed Drain Current ¹		I_{DM}	150	
Continuous Drain Current	$T_A = 25\text{ °C}$	I_D	14	
	$T_A = 70\text{ °C}$		11	
Avalanche Current		I_{AS}	36	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	65	mJ
Power Dissipation	$T_C = 25\text{ °C}$	P_D	62.5	W
	$T_C = 100\text{ °C}$		25	
Power Dissipation	$T_A = 25\text{ °C}$	P_D	2.5	W
	$T_A = 70\text{ °C}$		1.6	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	Steady-State	$R_{\theta JA}$		50	°C / W
Junction-to-Case	Steady-State	$R_{\theta JC}$		2	

¹Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ °C}$, Unless Otherwise Noted)

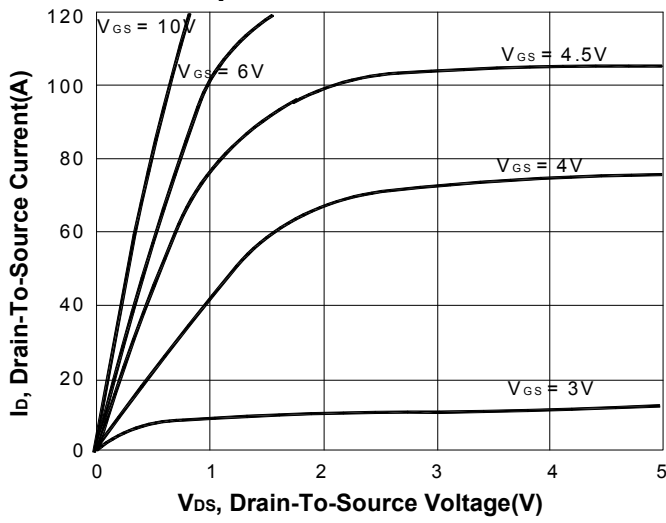
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2	1.7	3.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			±100	nA

Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$			1	μA
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 55\text{ }^\circ C$			10	
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 15A$		9.5	11.5	$m\Omega$
		$V_{GS} = 10V, I_D = 20A$		5.7	7.2	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 15V, I_D = 17A$		57		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		1150		pF
Output Capacitance	C_{oss}			270		
Reverse Transfer Capacitance	C_{rss}			170		
Gate Resistance	R_g	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		1.4		Ω
Total Gate Charge ²	Q_g	$V_{GS} = 10V$	$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = 10V, I_D = 20A$		25	nC
		$V_{GS} = 4.5V$			11	
Gate-Source Charge ²	Q_{gs}			4.5		
Gate-Drain Charge ²	Q_{gd}			7		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DS} = 15V, I_D \cong 20A, V_{GS} = 10V, R_{GEN} = 6\Omega$			17.5	
Rise Time ²	t_r			10		
Turn-Off Delay Time ²	$t_{d(off)}$			36		
Fall Time ²	t_f			11		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25\text{ }^\circ C$)						
Continuous Current	I_S				30	A
Forward Voltage ¹	V_{SD}	$I_F = 20A, V_{GS} = 0V$			1.2	V
Reverse Recovery Time	t_{rr}	$I_F = 20A, di_F/dt = 100A / \mu S$		30	55	nS

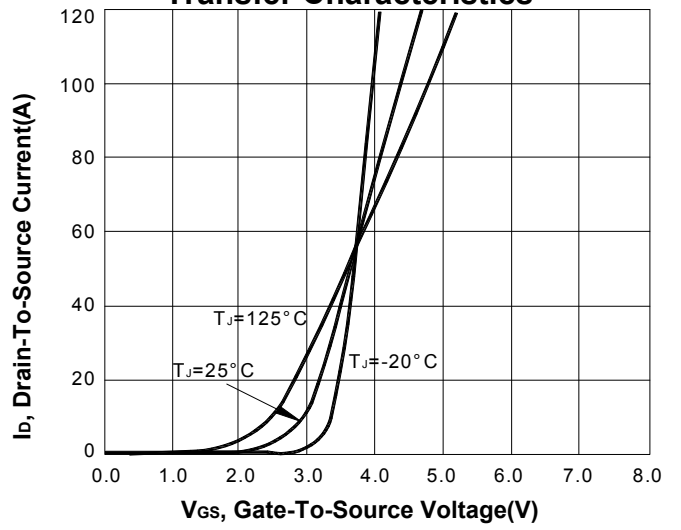
¹Pulse test : Pulse Width $\leq 300\ \mu sec$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

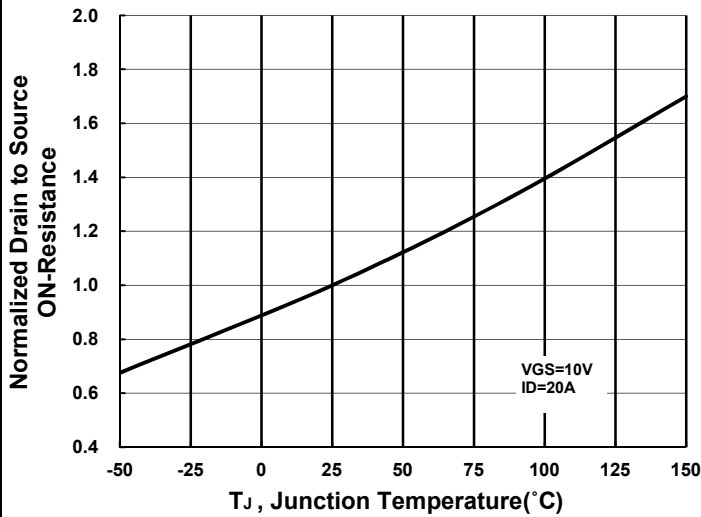
Output Characteristics



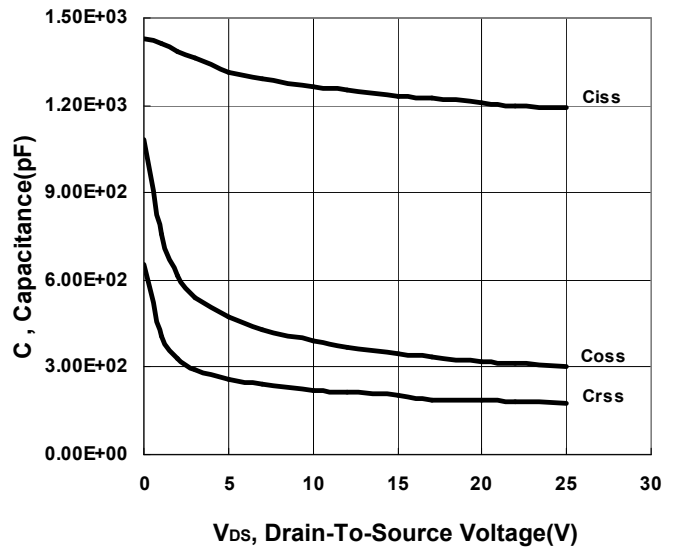
Transfer Characteristics



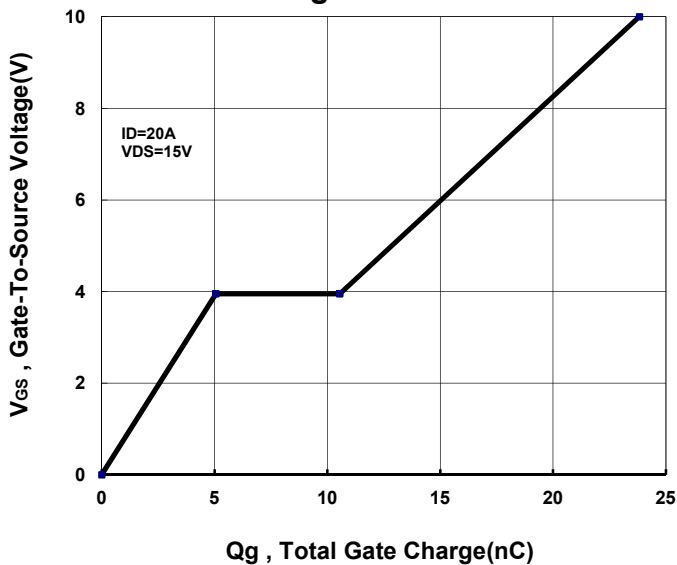
On-Resistance VS Temperature



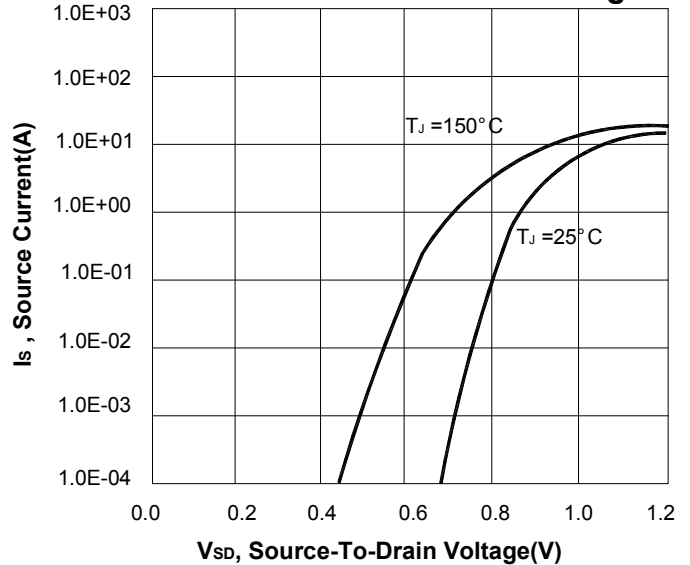
Capacitance Characteristic



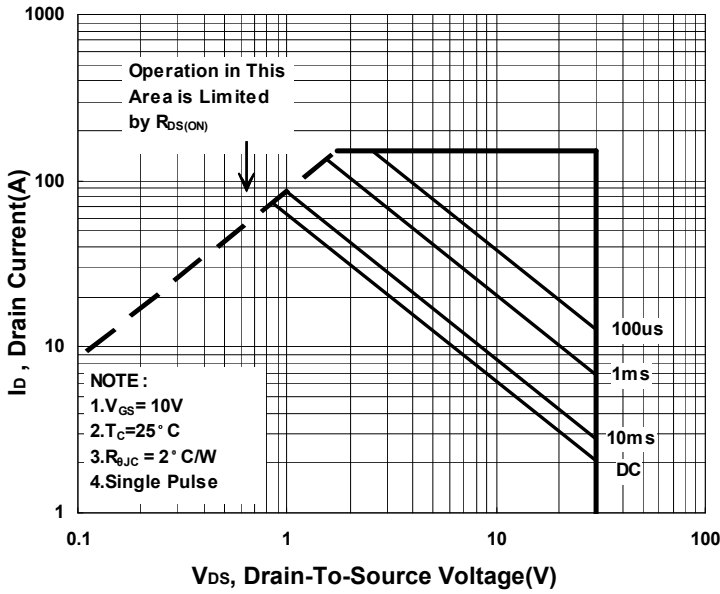
Gate charge Characteristics



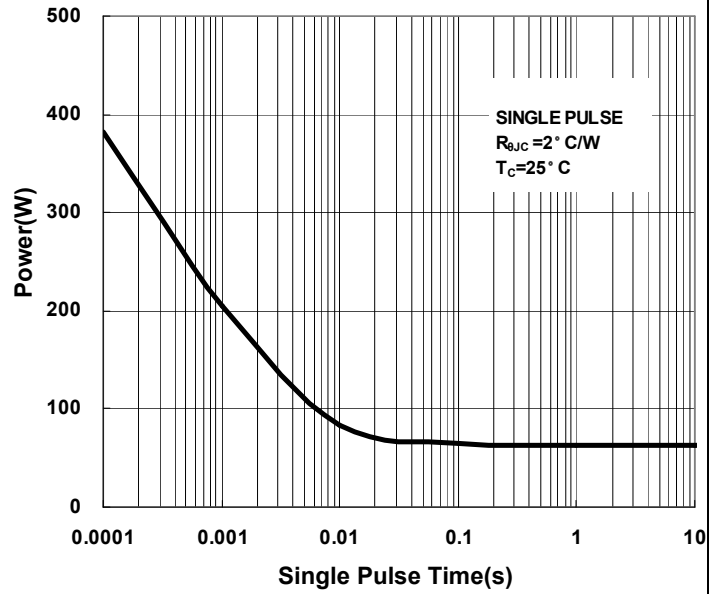
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

